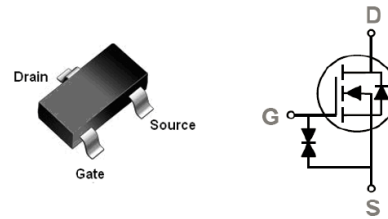


N Channel Advanced Power MOSFET

Features

- Low $R_{DS(on)}$ @ $V_{GS}=10V$
- 5V Logic Level Control
- N Channel SOT23 Package
- HMB ESD Protection 2KV
- Pb-Free, RoHS Compliant



SOT23

Applications

- LED Lighting Application,
- ON/OFF switch
- Networking

Order Information

Product	Package	Marking	Packing
2N7002K	SOT23	702	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit	
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage	±20	V	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	60	V	
T _J	Maximum Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-50 to 150	°C	
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested①	T _A =25°C	1.8	A
I _D	Continuous Drain Current	T _A =25°C	0.5	A
		T _A =70°C	0.4	
P _D	Maximum Power Dissipation	T _A =25°C	0.3	W
		T _A =70°C	0.2	
R _{θJA}	Thermal Resistance Junction-Ambient	400	°C/W	

N Channel Advanced Power MOSFET

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =60V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =50V, V _{GS} =0V	--	--	100	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±10	uA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =10V, I _D =0.5A	--	1.9	3	Ω
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =4.5V, I _D =0.3A	--	2.4	4	Ω
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	--	23.8	--	pF
C _{oss}	Output Capacitance		--	3.9	--	pF
C _{rss}	Reverse Transfer Capacitance		--	1.5	--	pF
Q _g	Total Gate Charge	V _{DS} =30V I _D =0.5A, V _{GS} =10V	--	0.93	--	nC
Q _{gs}	Gate Source Charge		--	0.18	--	nC
Q _{gd}	Gate Drain Charge		--	0.31	--	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =30V, I _D =0.3A, R _G =3.3Ω, V _{GS} =10V	--	6	--	ns
t _r	Turn on Rise Time		--	3.5	--	ns
t _{d(off)}	Turn Off Delay Time		-	20	--	ns
t _f	Turn Off Fall Time		--	5.9	--	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C	--	--	0.2	A
V _{SD}	Forward on voltage②	T _j =25°C, I _{SD} =0.5A, V _{GS} =0V	--	0.78	1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

N Channel Advanced Power MOSFET

Typical Characteristics

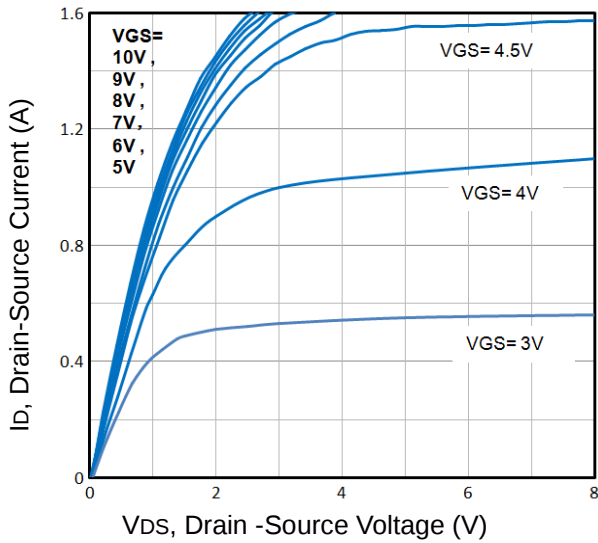


Fig1. Typical Output Characteristics

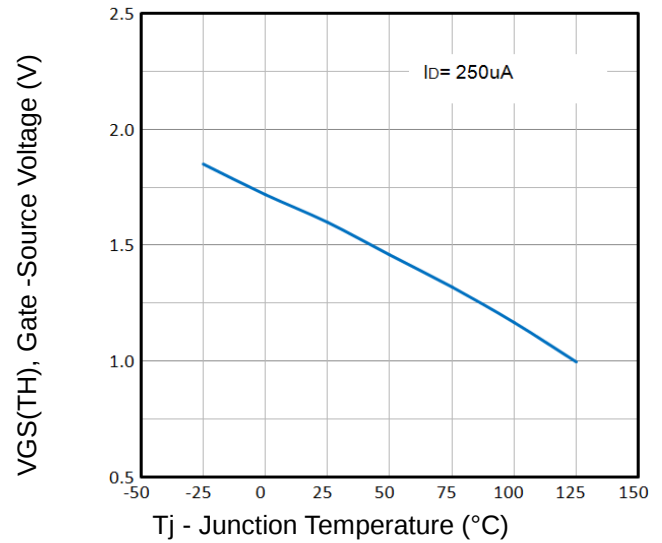


Fig2. Normalized Threshold Voltage Vs. Temperature

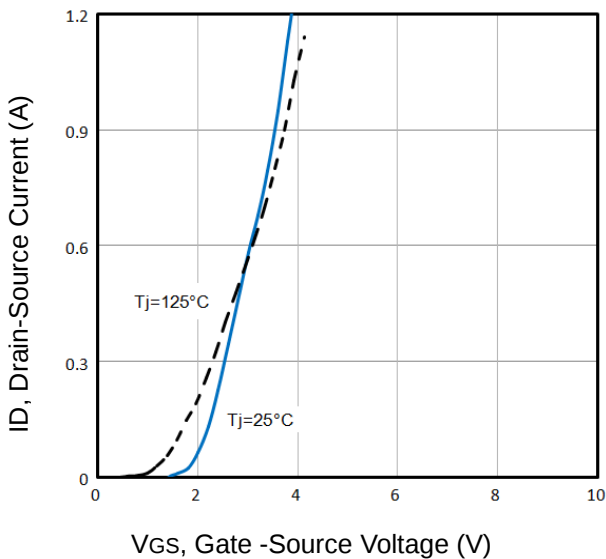


Fig3. Typical Transfer Characteristics

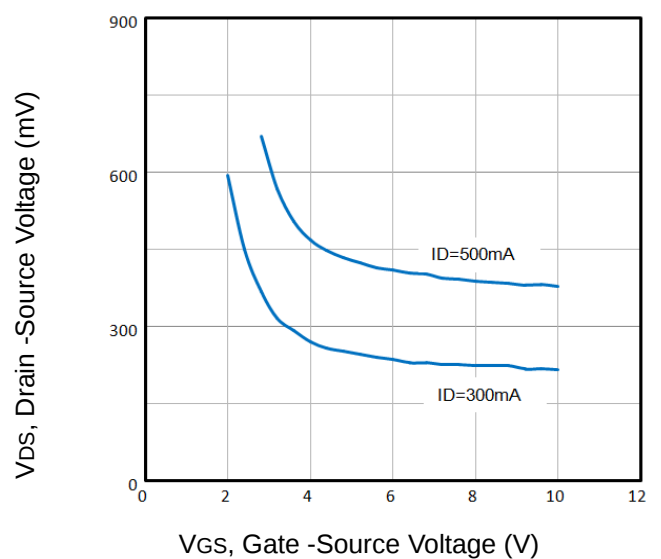


Fig4. Drain-Source Voltage vs Gate-Source Voltage

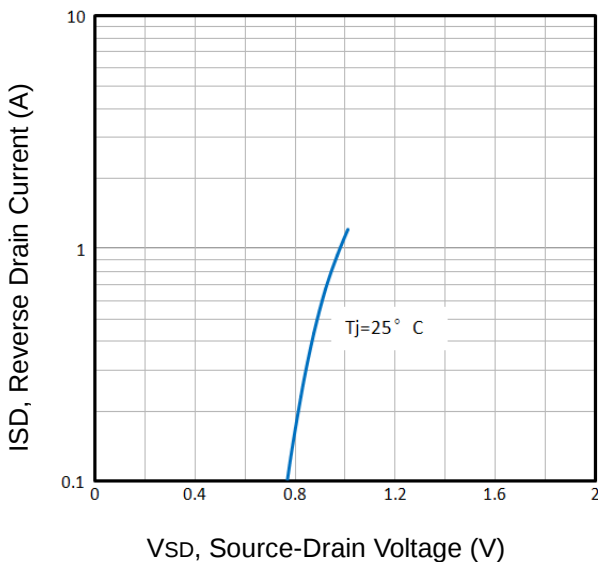


Fig5. Typical Source-Drain Diode Forward Voltage

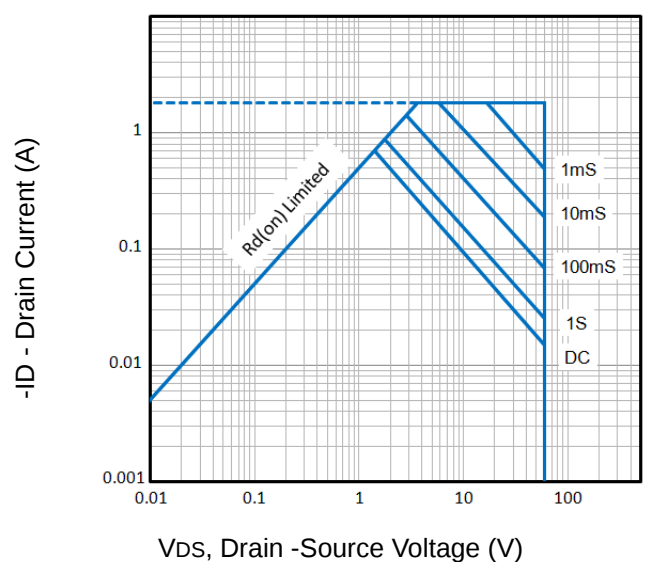


Fig6. Maximum Safe Operating Area

N Channel Advanced Power MOSFET

Typical Characteristics

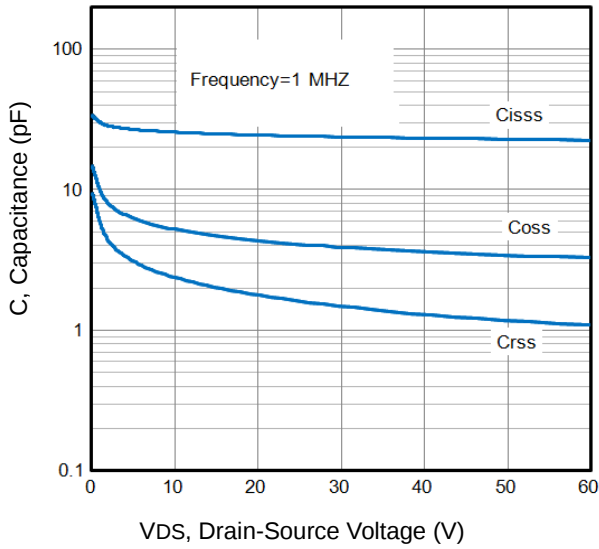


Fig7. Typical Capacitance Vs. Drain-Source Voltage

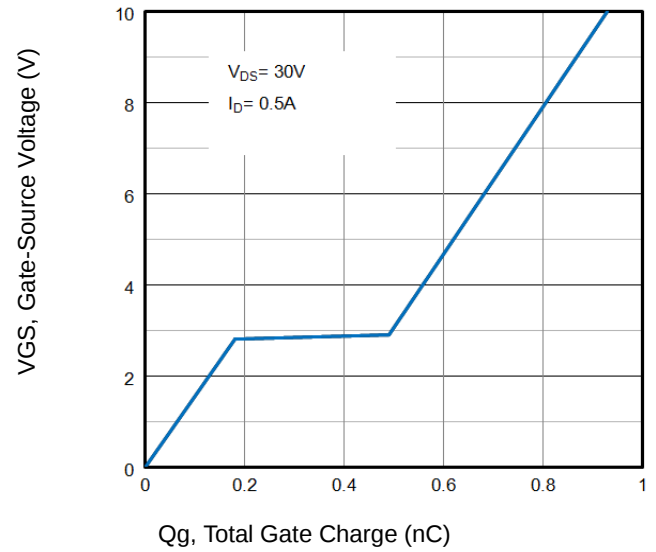


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

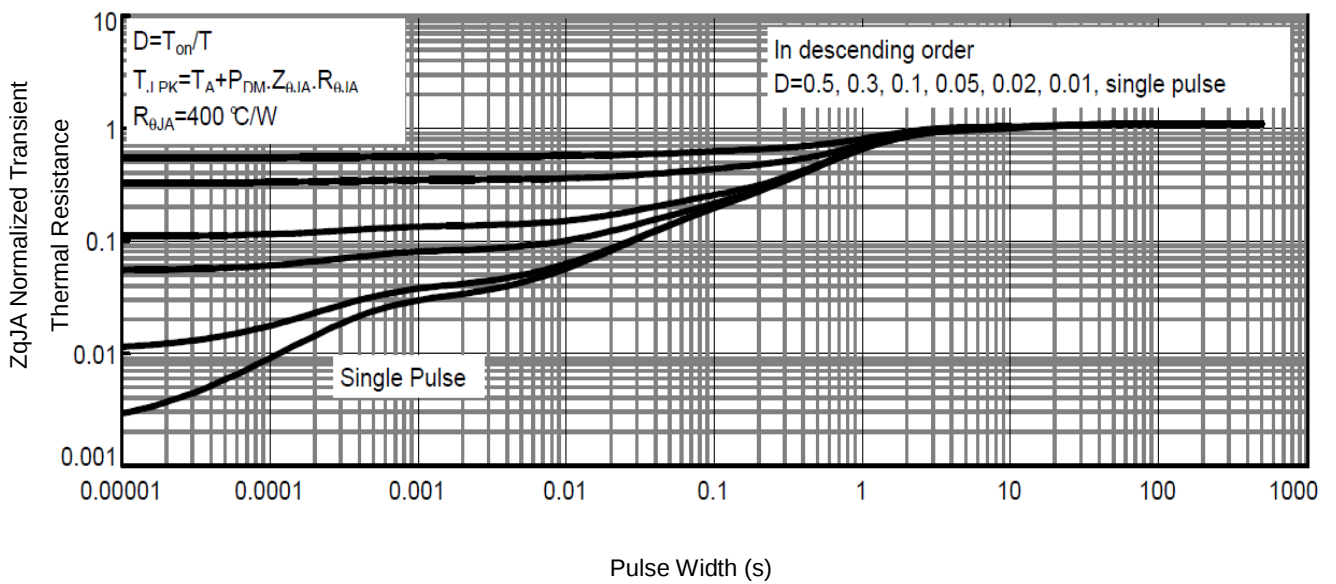


Fig9. Normalized Maximum Transient Thermal Impedance

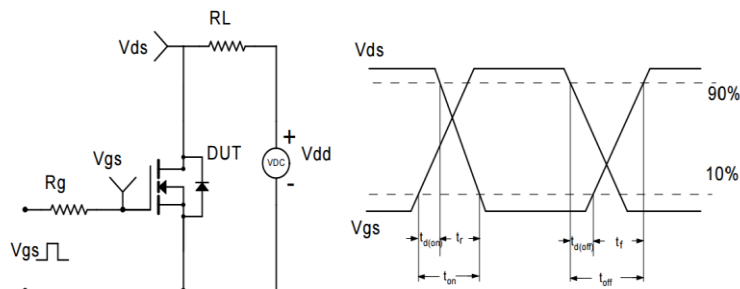
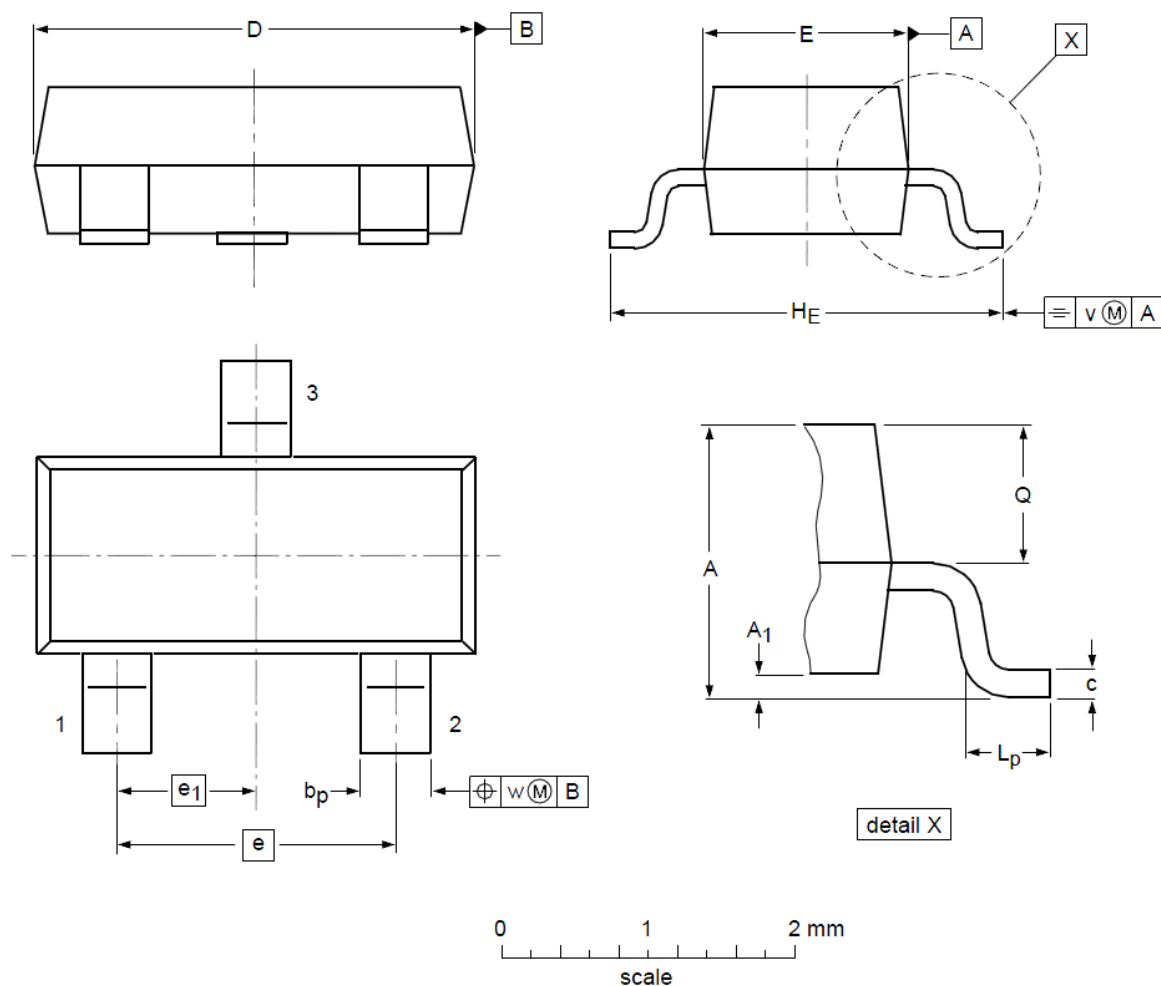


Fig10. Switching Time Test Circuit and waveforms

SOT23 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				